

N-channel 30 V, 4.2 m Ω logic level MOSFET in LFPAK33 using NextPowerS3 Technology

11 August 2015

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK33 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G, Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	65	W



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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Tj	junction temperature		-55	-	175	°C
Static char	acteristics		I			
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 20 A; T_j = 25 °C; Fig. 10	-	4.5	5.7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	3.45	4.3	mΩ
Dynamic cl	haracteristics	· · ·				
Q _{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13	-	3.1	4.6	nC
Q _{G(tot)}	total gate charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13	-	9.2	13.8	nC
Source-dra	in diode	· · ·	I			_,
S	softness factor	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 15 \text{ V}; \frac{\text{Fig. 16}}{100}$	-	1.05	-	

[1] Continuous current is limited by package

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G-UTA
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information							
Type number Package							
	Name	Description	Version				
PSMN4R2-30MLD	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

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Marking 7.

Table 4. Marking codes	
Type number	Marking code
PSMN4R2-30MLD	4D230L

Limiting values 8.

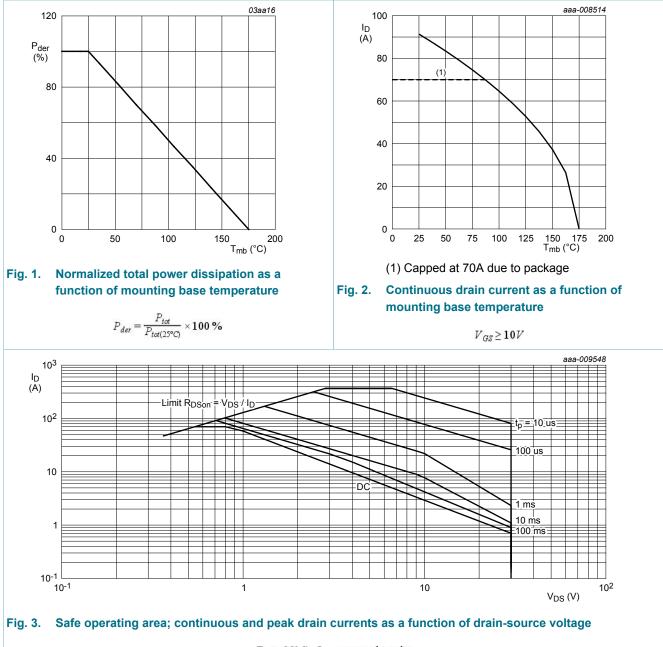
Symbol	Parameter	Conditions		Min	Мах	Un
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	65	W
ID	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	70	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	65	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	366	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	54	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	366	Α
Avalanche	ruggedness		1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 25 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω; unclamped; t_p = 122 μs	[2]	-	59	mJ

Continuous current is limited by package
Protected by 100% test

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PSMN4R2-30MLD

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$T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	2.09	2.32	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	Fig. 5	-	57	-	K/W
	from junction to ambient	<u>Fig. 6</u>	-	178	-	K/W

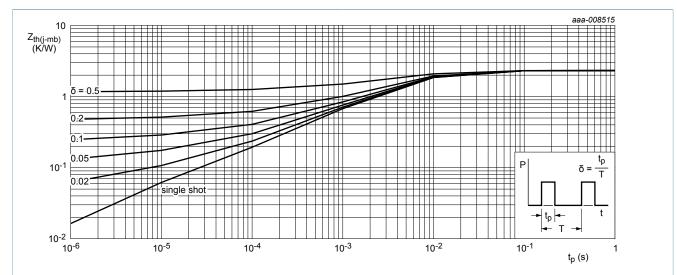
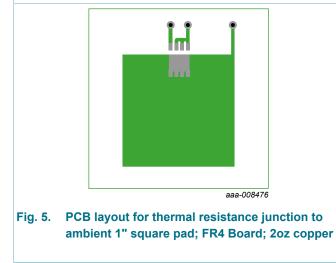


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



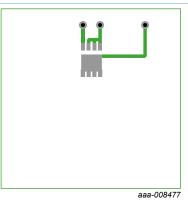


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

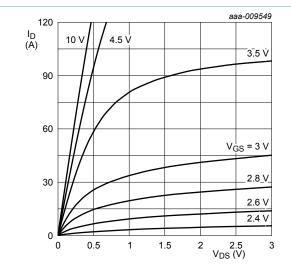
Table 7. Ch	naracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V _{(BR)DSS} drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C	1.2	1.7	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ΔV _{GS(th)} /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.1	-	mV/K
I _{DSS}	drain leakage current	V_{DS} = 24 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{DS} = 24 V; V_{GS} = 0 V; T_j = 125 °C	-	0.67	-	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 20 A; T _j = 25 °C; Fig. 10	-	4.5	5.7	mΩ
		V _{GS} = 4.5 V; I _D = 20 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	9.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	3.45	4.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	7.1	mΩ
R _G	gate resistance	f = 1 MHz	-	0.48	0.95	Ω
Dynamic cha	aracteristics		I			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	19.6	29.3	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	9.2	13.8	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	16.8	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V;	-	3.1	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	1.7	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	1.4	-	nC
Q _{GD}	gate-drain charge		-	3.1	4.6	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.9	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	1197	1795	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	848	1272	pF
C _{rss}	reverse transfer capacitance		-	87	130	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R _L = 0.6 Ω; V _{GS} = 4.5 V;	-	10.1	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	18.5	-	ns
t _{d(off)}	turn-off delay time	1	-	12	-	ns
t _f	fall time		-	8.7	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C		-	16.8	-	nC
Source-dra	in diode	·					
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.81	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;		-	26	52	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	15	30	nC
t _a	reverse recovery rise time			-	12.7	-	ns
t _b	reverse recovery fall time			-	13.3	-	ns
S	softness factor	-		-	1.05	-	



[1] includes capacitive recovery



 $T_j = 25^{\circ}C$

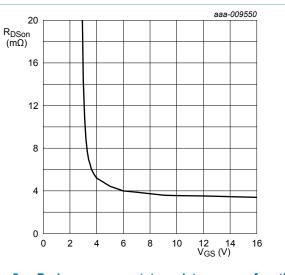
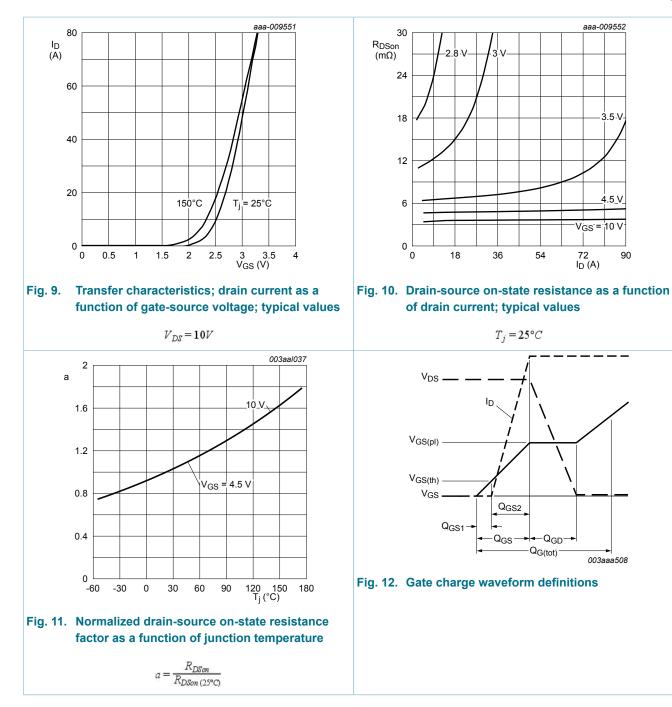


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; \ I_D = 25A$

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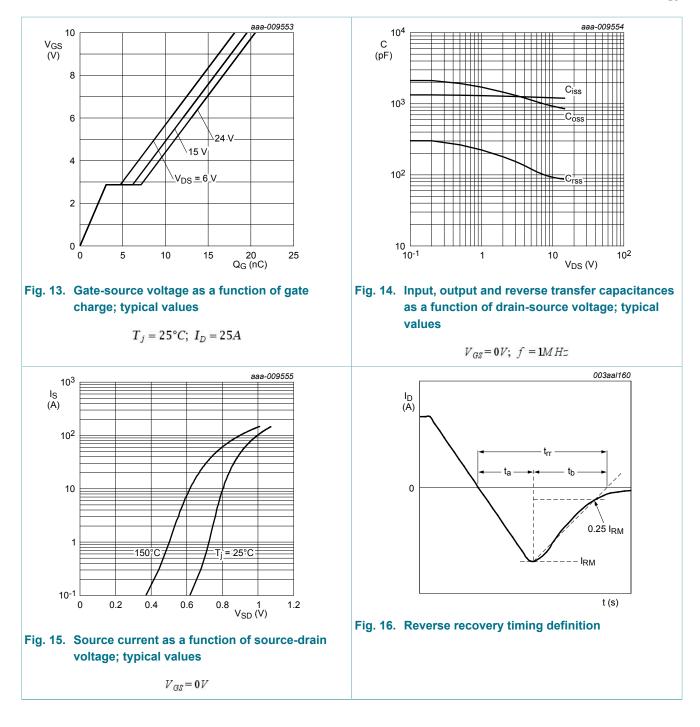
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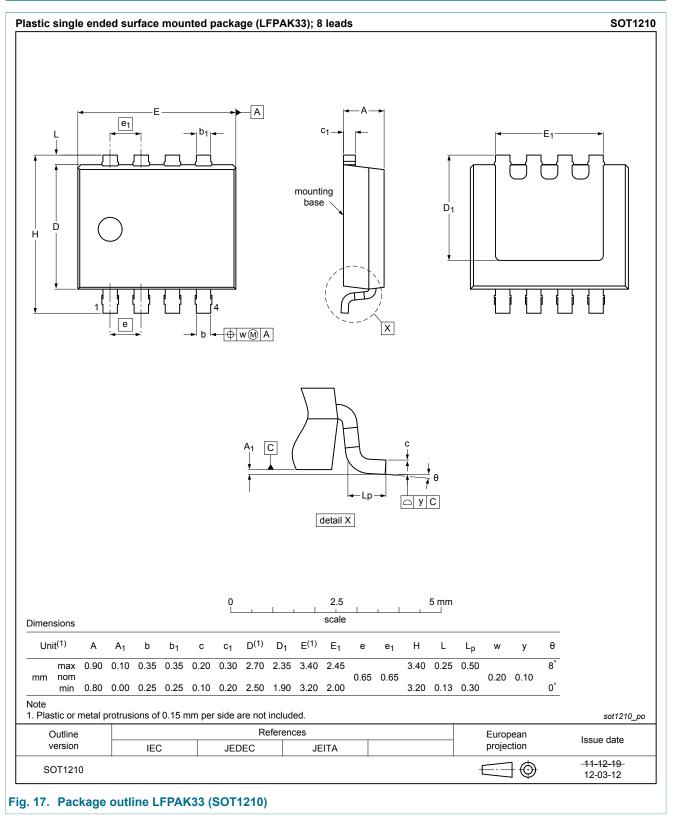
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11. Package outline



PSMN4R2-30MLD

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